



10th Nitride Semiconductor Application Workshop

~Activities for Nitride Semiconductors in the World~

Sponsored by: Aichi Science & Technology Foundation
 Supported by: The Japan Society of Applied Physics, Tokai Chapter
 Nagoya City Association for Industrial Technology
 Regional Conference for Utilization and Promotion of
 Achievements of the Tokai Region Knowledge Cluster Initiative

Date : Thursday, March 10, 2011 (10:00-17:20/Open: 9:30)
 Venue: 5 Floor, Big Hall, Nagoya Bankers Associations,
 2-4-2 Marunouchi, Naka-ku, Nagoya, Aichi, JAPAN

Phone: +81-(0)52-231-7851
 Participation Fee: Free *Maximum 200 participants

PROGRAM * Programs may change due to speakers' schedule.

10:00-10:10 Opening Talk

Y. Ohtsuka, Aichi Science & Technology Foundation

I. Activities for Nitride Semiconductors in the World (English) 10:10-17:20

1	10:10-10:40	E. Monroy, CEA Grenoble, France "Activities of Nitride Semiconductors in EU and Perspectives of Nitrides for Intersubband Optoelectronics"
2	10:40-11:10	F. Scholz, Ulm University, Germany "Activities of Nitride Semiconductors in EU with Special Focus on Non-/semipolar Activities"
3	11:10-11:40	G. Wang, Sun Yat-sen University, China "Activities of Nitride Semiconductors in China and Sun Yat-sen University"

11:40-13:00 (80min.) LUNCH

4	13:00-13:30	S. Arulkumaran, Nanyang Technological University, Singapore "Overview of Activities of Nitride Semiconductors in Singapore"
5	13:30-14:00	M. Higashiwaki, National Institution of Information and Commercial Technology "Activities of Nitride Semiconductors in USA; High Frequency GaN Electronic Devices "
6	14:00-14:30	E. Fujiwara, International Rectifier Japan "GaN Device Technology and Application"

14:30-14:50 (20min.) BREAK

II. Perspectives for GaN Power Devices (Japanese/ English Explanation by Receivers)

7	14:50-15:20	H. Shimizu, Research and Development Association for Future Electronic Devices "GaN and SiC; Expectation as Power Devices"
8	15:20-15:50	K. Matsumoto, TN EMC Ltd. "MOCVD Systems for Power Device Applications"
9	15:50-16:20	Y. Ikeda, Fuji Electric Holdings Co. "Packaging Technology for Power Devices"
10	16:20-16:50	M. Shimizu, Advanced Industrial Science and Technology (AIST) "Theoretical Performance Limits of GaN Power Devices"
11	16:50-17:20	M. Sugimoto, Toyota Motor Co. " Expectation of GaN/Si Power Devices for Automobiles"

17:30-18:30 BANQUET

Date & Time: 17:30-19:00 Thursday March 10, 2011
 Venue: Grand Shariot, 12 Floor, Airis Aichi
 Banquet Fee: 3,000 JPY *Please pay on-site.

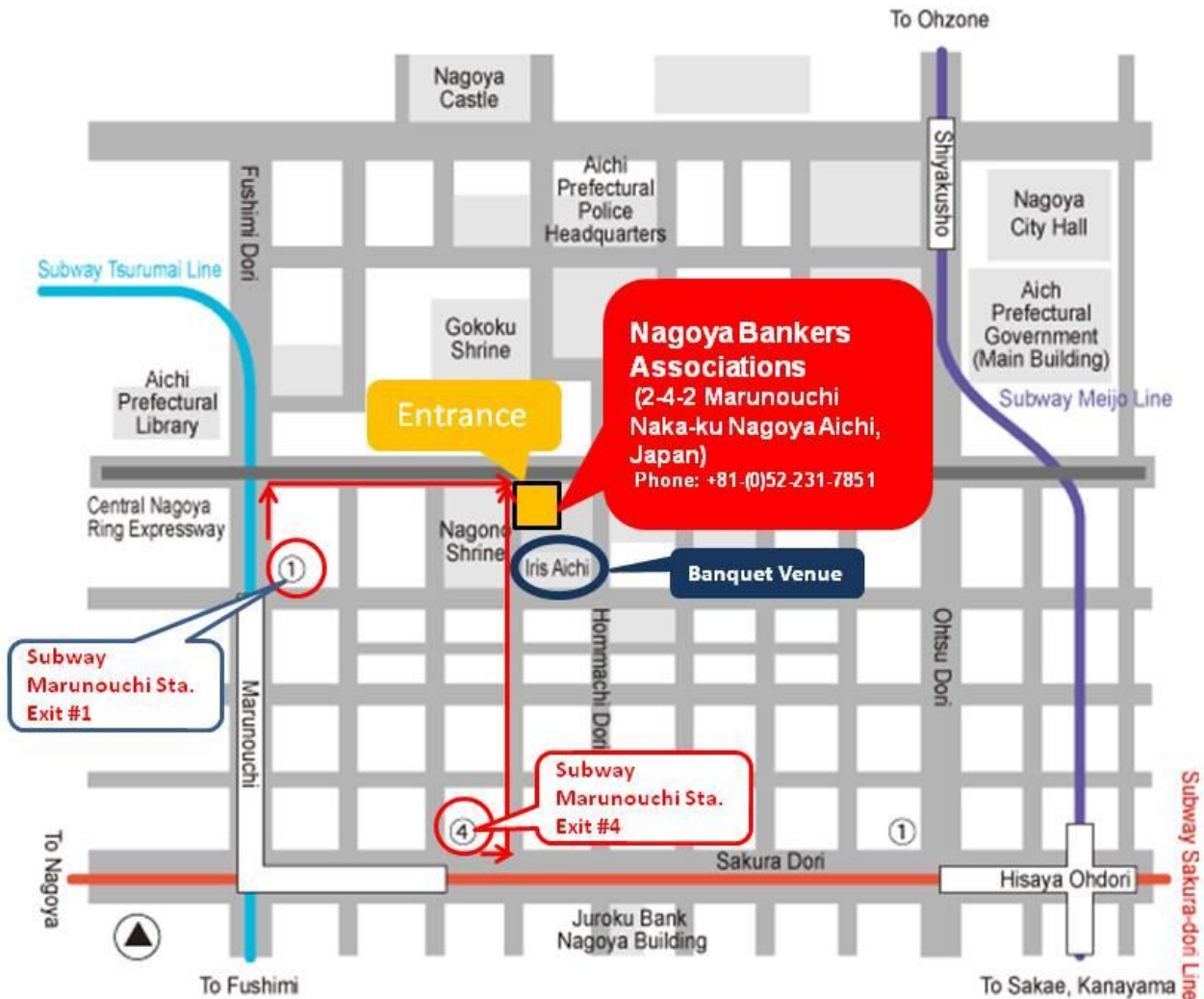
REGISTRATION

For those who would like to participate in this workshop, please email the following to; cluster2008@astf.or.jp
Email Title: 10 th Nitride Semiconductor Application Workshop Registration

1. Name
2. Affiliation
3. Address
4. Telephone Number and Fax Number
5. Email Address
6. Whether you would like to attend the banquet or not.

If you are presently attending the ISPlasma2011, please come to the inquiry desk for registration.

ACCESS



From Nagoya Station

*Take the subway/Sakura Dori Line, get off at Marunouchi Sta. Exit #4. *6 minutes walk to the venue.

*Take the subway/Tsurumai Line, get off at Marunouchi Sta. Exit #1. *5 minutes walk to the venue.

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